



JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

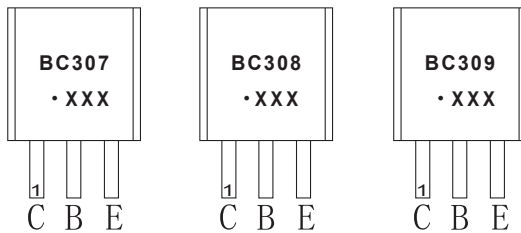
TO-92 Plastic-Encapsulate Transistors

BC307/308/309 TRANSISTOR (PNP)

FEATURES

● Amplifier dissipation NPN Silicon

MARKING



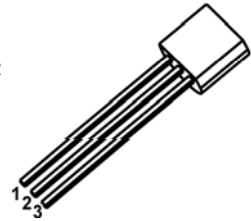
BC307,BC308,BC309=Device code

Solid dot=Green molding compound device,
if none,the normal device

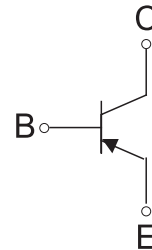
XXX=Code

TO-92

1. COLLECTOR
2. BASE
3. EMITTER



Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BC307	TO-92	Bulk	1000pcs/Bag
BC307-TA	TO-92	Tape	2000pcs/Box
BC308	TO-92	Bulk	1000pcs/Bag
BC308-TA	TO-92	Tape	2000pcs/Box
BC309	TO-92	Bulk	1000pcs/Bag
BC309-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CEO}	Collector-Emitter Voltage	BC307	-45	V
		BC308/309	-25	
V _{EBO}	Emitter-Base Voltage	BC307	-6	V
		BC308/309	-5	
I _C	Collector Current -Continuous	-0.1	A	
P _C	Collector Power Dissipation	500	mW	
R _{θ JA}	Thermal Resistance, Junction to Ambient	357	°C /W	
R _{θ JC}	Thermal Resistance, Junction to Case	125	°C /W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C	

ELECTRICAL CHARACTERISTICS

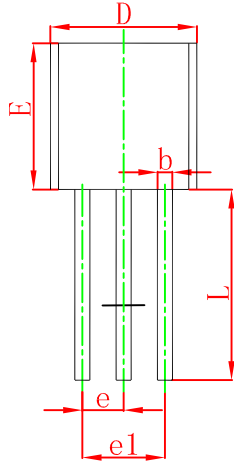
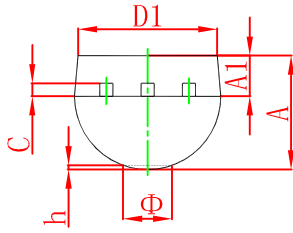
$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}$, $I_E=0$ BC307 BC308/309	-50 -30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-2\text{mA}$, $I_B=0$ BC307 BC308/309	-45 -25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}$, $I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-45\text{V}$, $I_E=0$ BC307 $V_{CB}=-25\text{V}$, $I_E=0$ BC308/309			-15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-15	nA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}$, $I_C=-2\text{mA}$	120		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}$, $I_B=-0.5\text{mA}$			-0.3	V
		$I_C=-100\text{mA}$, $I_B=-5\text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10\text{mA}$, $I_B=-0.5\text{mA}$			-0.75	V
		$I_C=-100\text{mA}$, $I_B=-5\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5\text{V}$, $I_C=-2\text{mA}$	-0.55		-0.75	V
Transition frequency	f_T	$V_{CE}=-5\text{V}$, $I_C=-10\text{mA}$, $f=50\text{MHz}$		130		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$, $I_E=0$, $f=1\text{MHz}$			6	pF
Noise figure	NF	$V_{CE}=-5\text{V}$, $I_C=-0.2\text{mA}$, $f=1\text{KHz}$, $R_G=2\text{K}\Omega$ BC307/BC308 BC309			10 4	dB
		$V_{CE}=-5\text{V}$, $I_C=-0.2\text{mA}$, $f=30-15\text{KHz}$, $R_G=2\text{K}\Omega$ BC309			4	

CLASSIFICATION OF h_{FE}

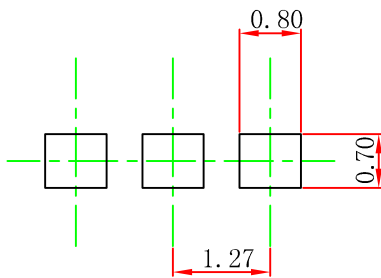
Rank	A	B	C
Range	120-220	180-460	380-800

TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



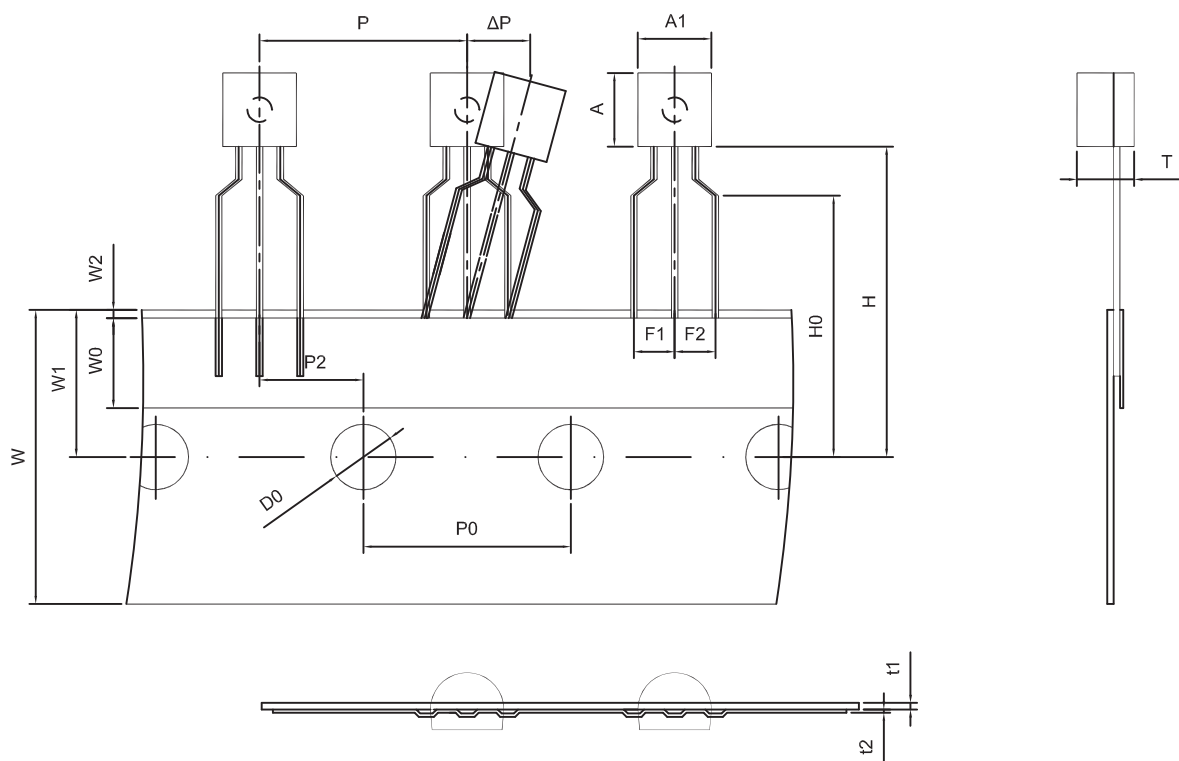
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

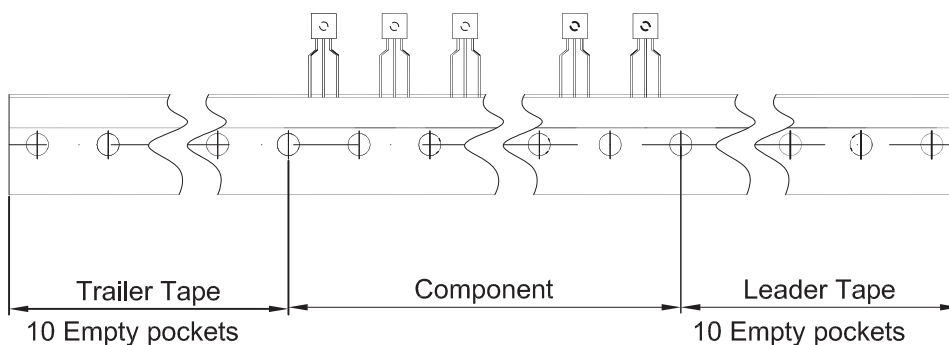
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TO-92 PACKAGE TAPING DIMENSION



Dimiensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250